

Mohamed Henini

List of Publications by Year in descending order

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28274

55
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43889

91
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882
all docs

882
docs citations

882
times ranked

8135
citing authors

#	ARTICLE	IF	CITATIONS
1	Photodegradation of organic pollutants RhB dye using UV simulated sunlight on ceria based TiO ₂ nanomaterials for antibacterial applications. Scientific Reports, 2016, 6, 38064.	3.3	353
2	Carrier thermal escape and retrapping in self-assembled quantum dots. Physical Review B, 1999, 60, 8276-8283.	3.2	313
3	Two Dimensional Electrons in a Lateral Magnetic Superlattice. Physical Review Letters, 1995, 74, 3009-3012.	7.8	255
4	Real-time scanning Hall probe microscopy. Applied Physics Letters, 1996, 69, 1324-1326.	3.3	236
5	Paramagnetic Meissner effect in small superconductors. Nature, 1998, 396, 144-146.	27.8	232
6	Rare earth element (REE) lanthanum doped zinc oxide (La: ZnO) nanomaterials: Synthesis structural optical and antibacterial studies. Journal of Alloys and Compounds, 2017, 723, 1155-1161.	5.5	229
7	Probing the hole dispersion curves of a quantum well using resonant magnetotunneling spectroscopy. Physical Review Letters, 1991, 66, 1749-1752.	7.8	213
8	Resonant tunneling through the bound states of a single donor atom in a quantum well. Physical Review Letters, 1992, 68, 1754-1757.	7.8	213
9	Resistance Resonance Effects through Magnetic Edge States. Physical Review Letters, 2000, 84, 2231-2234.	7.8	203
10	Temperature dependence of the optical properties of InAs/AlGaAs self-organized quantum dots. Physical Review B, 1999, 59, 5064-5068.	3.2	202
11	Magnetic field studies of elastic scattering and optic-phonon emission in resonant-tunneling devices. Physical Review B, 1989, 39, 3438-3441.	3.2	187
12	Magnetoresistance of a two-dimensional electron gas due to a single magnetic barrier and its use for nanomagnetometry. Applied Physics Letters, 1999, 74, 2507-2509.	3.3	183
13	A one-dimensional chain state of vortex matter. Nature, 2001, 414, 728-731.	27.8	169
14	Imaging the Electron Wave Function in Self-Assembled Quantum Dots. Science, 2000, 290, 122-124.	12.6	168
15	Fermi-edge singularity in resonant tunneling. Physical Review Letters, 1994, 72, 2061-2064.	7.8	160
16	Electron-concentration-dependent quantum-well luminescence: Evidence for a negatively charged exciton. Physical Review B, 1995, 51, 7969-7972.	3.2	149
17	Spin Excitations of a Two-Dimensional Electron Gas in the Limit of Vanishing Landau Level Factor. Physical Review Letters, 1996, 77, 4604-4607.	7.8	138
18	High Temperature Gate Control of Quantum Well Spin Memory. Physical Review Letters, 2003, 91, 246601.	7.8	137

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19	Magnetoresistance of a two-dimensional electron gas in a strong periodic potential. Physical Review B, 1990, 42, 9229-9232.	3.2	136
20	Evaluation on La ₂ O ₃ garlanded ceria heterostructured binary metal oxide nanoplates for UV/ visible light induced removal of organic dye from urban wastewater. South African Journal of Chemical Engineering, 2018, 26, 49-60.	2.4	124
21	Coherent Terahertz Sound Amplification and Spectral Line Narrowing in a Stark Ladder Superlattice. Physical Review Letters, 2010, 104, 085501.	7.8	121
22	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. Nature, 2004, 428, 726-730.	27.8	117
23	Resonant magnetotunneling through individual self-assembled InAs quantum dots. Physical Review B, 1996, 54, 16401-16404.	3.2	114
24	Acoustic Phonon Emission from a Weakly Coupled Superlattice under Vertical Electron Transport: Observation of Phonon Resonance. Physical Review Letters, 2006, 96, 215504.	7.8	112
25	Sequential tunneling due to intersubband scattering in double-barrier resonant tunneling devices. Applied Physics Letters, 1988, 52, 212-214.	3.3	101
26	Observation of intrinsic bistability in resonant tunnelling devices. Electronics Letters, 1988, 24, 1190.	1.0	97
27	Transition metal titanium (Ti) doped LaFeO ₃ nanoparticles for enhanced optical structural and magnetic properties. Journal of Alloys and Compounds, 2017, 712, 870-877.	5.5	96
28	Temperature dependence of the photoluminescence emission from thiol-capped PbS quantum dots. Applied Physics Letters, 2007, 90, 101913.	3.3	95
29	Probing the wave function of quantum confined states by resonant magnetotunneling. Physical Review B, 1993, 48, 5664-5667.	3.2	92
30	Scanning Hall probe microscopy of superconductors and magnetic materials. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1202.	1.6	86
31	Electronic structure of self-assembled InAs quantum dots in GaAs matrix. Applied Physics Letters, 1998, 73, 1092-1094.	3.3	86
32	Probing the quantum states of self-assembled InAs dots by magnetotunneling spectroscopy. Physical Review B, 2002, 65, .	3.2	85
33	Photoluminescence of negatively charged excitons in high magnetic fields. Physical Review B, 1999, 59, 2927-2931.	3.2	84
34	Fine Structure in Magnetization of Individual Fluxoid States. Physical Review Letters, 2000, 85, 1528-1531.	7.8	84
35	Synthesis, structural, magnetic and optical properties of nanocrystalline ZnFe ₂ O ₄ . Physica B: Condensed Matter, 2011, 406, 1989-1994.	2.7	84
36	Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. Physical Review B, 1990, 41, 10754-10766.	3.2	80

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37	Optical anisotropy in arrow-shaped InAs quantum dots. Physical Review B, 1998, 57, R6815-R6818.	3.2	80
38	Observation of giant magnetoresistance due to open orbits in hybrid semiconductor/ferromagnet devices. Physical Review B, 1997, 55, R16037-R16040.	3.2	79
39	Enhanced spin-relaxation time due to electron-electron scattering in semiconductor quantum wells. Physical Review B, 2007, 75, .	3.2	76
40	Enhanced magnetic properties of polymer-magnetic nanostructures synthesized by ultrasonication. Journal of Alloys and Compounds, 2017, 720, 395-400.	5.5	76
41	Observation of space-charge bulk-up and thermalisation in an asymmetric double-barrier resonant tunnelling structure. Journal of Physics Condensed Matter, 1989, 1, 10605-10611.	1.8	75
42	Photocurrent Enhancement in Hybrid Nanocrystal Quantum-Dot $p-i-n$ Photovoltaic Devices. Physical Review Letters, 2009, 102, 077402.	7.8	72
43	Charge build-up and intrinsic bistability in an asymmetric resonant-tunnelling structure. Semiconductor Science and Technology, 1988, 3, 1060-1062.	2.0	71
44	Gated resonant tunnelling devices. Electronics Letters, 1991, 27, 134.	1.0	71
45	All-optical measurement of Rashba coefficient in quantum wells. Physical Review B, 2008, 77, .	3.2	71
46	Photoluminescence spectroscopy of self-assembled InAs quantum dots in strong magnetic field and under high pressure. Applied Physics Letters, 1997, 70, 505-507.	3.3	68
47	Energy levels in self-assembled InAs/GaAs quantum dots above the pressure-induced $\tilde{\nu}^*$ crossover. Physical Review B, 1998, 58, R4250-R4253.	3.2	66
48	Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. Solid-State Electronics, 1989, 32, 1101-1108.	1.4	63
49	Role of point defects in the silicon diffusion in GaAs and Al _{0.3} Ga _{0.7} As and in the related superlattice disordering. Journal of Applied Physics, 1992, 71, 2225-2237.	2.5	62
50	The oscillatory magnetoresistance of electrons in a square superlattice potential. Journal of Physics Condensed Matter, 1989, 1, 8257-8262.	1.8	60
51	Measuring the Probability Density of Quantum Confined States. Physical Review Letters, 1995, 75, 1996-1999.	7.8	60
52	Cyclotron resonance in ultra-low-hole-density narrow p-type GaAs/(Al,Ga)As quantum wells. Physical Review B, 1997, 55, 2503-2511.	3.2	60
53	Direct Observation of Melting of the Vortex Solid in Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ Single Crystals. Physical Review Letters, 1998, 80, 3610-3613.	7.8	58
54	Observation of spin splitting in single InAs self-assembled quantum dots in AlAs. Applied Physics Letters, 1998, 73, 354-356.	3.3	57

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55	Temperature dependence of large positive magnetoresistance in hybrid ferromagnetic/semiconductor devices. Applied Physics Letters, 1998, 72, 1724-1726.	3.3	55
56	Carrier localization in GaBiAs probed by photomodulated transmittance and photoluminescence. Journal of Applied Physics, 2009, 106, 023518.	2.5	55
57	Interface Induced Uniaxial Magnetic Anisotropy in Amorphous CoFeB Films on AlGaAs(001). Physical Review Letters, 2008, 100, 117201.	7.8	54
58	Current bistability in double-barrier resonant-tunneling devices. Physical Review B, 1989, 39, 6205-6207.	3.2	53
59	Influence of reaction time and synthesis temperature on the physical properties of ZnO nanoparticles synthesized by the hydrothermal method. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	53
60	Molecular beam epitaxy of GaBiAs on (311)B GaAs substrates. Applied Physics Letters, 2007, 91, 251909.	3.3	50
61	Landau-Level Spectroscopy of a Two-Dimensional Electron System by Tunneling through a Quantum Dot. Physical Review Letters, 2000, 84, 729-732.	7.8	49
62	Oscillatory Dyakonov-Perel spin dynamics in two-dimensional electron gases. Physical Review B, 2007, 76, .	3.2	49
63	Phonon Absorption at the Magnetoroton Minimum in the Fractional Quantum Hall Effect. Physical Review Letters, 1995, 74, 2339-2342.	7.8	47
64	Influence of the As overpressure during the molecular beam epitaxy growth of Si-doped (211)A and (311)A GaAs. Applied Physics Letters, 1995, 66, 2846-2848.	3.3	47
65	Self-sustained current oscillation above 100 GHz in a GaAs/AlAs superlattice. Applied Physics Letters, 1999, 74, 2179-2181.	3.3	47
66	Thermal effects in quantum dot lasers. Journal of Applied Physics, 1999, 85, 625-627.	2.5	47
67	Spin-orbit fields in asymmetric (001)-oriented GaAs/Al quantum wells. Physical Review B, 2011, 83, . $\langle \sigma_x \rangle = \frac{1}{2} \langle \sigma_y \rangle \hat{z}$	3.2	47
68	Optical properties and device applications of (InGa)As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 1998, 73, 1415-1417.	3.3	46
69	Structural and optical characterization of self-assembled InAs-GaAs quantum dots grown on high index surfaces. Microelectronics Journal, 1997, 28, 933-938.	2.0	45
70	Piezoelectric effects in In _{0.5} Ga _{0.5} As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 2000, 77, 2979-2981.	3.3	45
71	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. Physical Review B, 1990, 42, 3069-3076.	3.2	44
72	Nonradiative exciton energy transfer in hybrid organic-inorganic heterostructures. Physical Review B, 2008, 77, .	3.2	44

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73	Thermopower measurements of the coupling of phonons to electrons and composite fermions. Physical Review B, 1998, 58, 2017-2025.	3.2	43
74	High-temperature light emission from InAs quantum dots. Applied Physics Letters, 1999, 75, 814-816.	3.3	42
75	Hall anomaly of diffusive magnetic waveguides. Physical Review B, 2003, 67, .	3.2	42
76	Piezoelectric-induced quantum-confined Stark effect in self-assembled InAs quantum dots grown on (N11) GaAs substrates. Applied Physics Letters, 2000, 77, 1982-1984.	3.3	41
77	Improvement of the nutritional quality of foods as a public health tool. Public Health, 2011, 125, 717-724.	2.9	41
78	Effect of As overpressure on Si-doped (111)A GaAs grown by molecular beam epitaxy: a photoluminescence study. Semiconductor Science and Technology, 1992, 7, 1504-1507.	2.0	40
79	D ⁺ centers probed by resonant tunneling spectroscopy. Physical Review B, 1996, 53, 9554-9557.	3.2	40
80	Even-Denominator Filling Factors in the Thermoelectric Power of a Two-Dimensional Electron Gas. Physical Review Letters, 1996, 76, 3630-3633.	7.8	40
81	Stark shift in electroluminescence of individual InAs quantum dots. Applied Physics Letters, 2000, 76, 3932-3934.	3.3	39
82	Magnetoresistance oscillations due to internal Landau band structure of a two-dimensional electron system in a periodic magnetic field. Physical Review B, 2001, 64, .	3.2	38
83	Terahertz phonon optics in GaAs/AlAs superlattice structures. Physical Review B, 2003, 68, .	3.2	38
84	Distribution of bismuth atoms in epitaxial GaAsBi. Applied Physics Letters, 2011, 98, 101902.	3.3	38
85	Imaging nonequilibrium phonon-induced backscattering in the quantum Hall regime. Physical Review Letters, 1992, 69, 1684-1686.	7.8	37
86	Quantum Hall ferromagnet at high filling factors: A magnetic-field-induced Stoner transition. Physical Review B, 2005, 72, .	3.2	37
87	Resonant Magnetotunneling via One-Dimensional Quantum Confined States. Physical Review Letters, 1994, 73, 1146-1149.	7.8	36
88	Carrier thermalization within a disordered ensemble of self-assembled quantum dots. Physical Review B, 2000, 62, 11084-11088.	3.2	36
89	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. Applied Physics Letters, 2002, 81, 661-663.	3.3	36
90	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. Applied Physics Letters, 2003, 83, 3069-3071.	3.3	36

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91	Properties and applications of quantum dot heterostructures grown by molecular beam epitaxy. <i>Nanoscale Research Letters</i> , 2006, 1, 32-45.	5.7	36
92	Growth and electrical transport properties of very high mobility two-dimensional hole gases displaying persistent photoconductivity. <i>Applied Physics Letters</i> , 1994, 65, 2054-2056.	3.3	35
93	Terahertz response of zero-dimensional states in resonant tunneling diodes. <i>Applied Physics Letters</i> , 1995, 67, 3453-3455.	3.3	35
94	Magnetophotoluminescence of negatively charged excitons in narrow quantum wells. <i>Physical Review B</i> , 2001, 63, .	3.2	35
95	Submicrometer resonant tunnelling diodes fabricated by photolithography and selective wet etching. <i>Applied Physics Letters</i> , 1994, 65, 1124-1126.	3.3	34
96	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. <i>Applied Physics Letters</i> , 2000, 77, 3556-3558.	3.3	34
97	Generation and propagation of monochromatic acoustic phonons in gallium arsenide. <i>Applied Physics Letters</i> , 2002, 81, 3497-3499.	3.3	34
98	Radioluminescence and photoluminescence characterization of Eu and Tb doped barium stannate phosphor ceramics. <i>Journal of Alloys and Compounds</i> , 2014, 590, 417-423.	5.5	34
99	Fabrication of novel transparent Co ₃ O ₄ -TiO ₂ nanowires p-n heterojunction diodes for multiband photodetection applications. <i>Journal of Alloys and Compounds</i> , 2017, 712, 7-14.	5.5	34
100	Magnetoresistance and Hall magnetometry of single submicron ferromagnetic structures. <i>Journal of Applied Physics</i> , 2000, 87, 5986-5988.	2.5	33
101	Integrated piezoresistive sensors for atomic force-guided scanning Hall probe microscopy. <i>Applied Physics Letters</i> , 2003, 82, 3538-3540.	3.3	33
102	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. <i>Physical Review B</i> , 2004, 70, .	3.2	33
103	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photorefectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , 2006, 100, 093522.	2.5	33
104	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. <i>Physical Review Letters</i> , 2012, 108, 226601.	7.8	33
105	Surface effects of vapour-liquid-solid driven Bi surface droplets formed during molecular-beam-epitaxy of GaAsBi. <i>Scientific Reports</i> , 2016, 6, 28860.	3.3	33
106	From Khoi-San indigenous knowledge to bioengineered CeO ₂ nanocrystals to exceptional UV-blocking green nanocosmetics. <i>Scientific Reports</i> , 2022, 12, 3468.	3.3	33
107	Adsorbed and substituted Sb dimers on GaAs(001). <i>Physical Review B</i> , 1996, 53, R16148-R16151.	3.2	32
108	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. <i>Journal of Crystal Growth</i> , 2003, 251, 155-160.	1.5	32

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109	Resistance Noise Scaling in a Dilute Two-Dimensional Hole System in GaAs. Physical Review Letters, 2003, 90, 076402.	7.8	32
110	Scanning capacitance imaging of compressible and incompressible quantum Hall effect edge strips. New Journal of Physics, 2012, 14, 083015.	2.9	31
111	Solid state synthesis of SrAl ₂ O ₄ :Mn ²⁺ co-doped with Nd ³⁺ phosphor and its optical properties. Journal of Luminescence, 2013, 144, 128-132.	3.1	31
112	Band gap and partial density of states for ZnO: Under high pressure. Journal of Alloys and Compounds, 2015, 619, 812-819.	5.5	31
113	Hall Photovoltage Imaging of the Edge of a Quantum Hall Device. Physical Review Letters, 1997, 79, 5114-5117.	7.8	30
114	Fundamental Relation between Electrical and Thermoelectric Transport Coefficients in the Quantum Hall Regime. Physical Review Letters, 1997, 78, 4621-4624.	7.8	30
115	InAs quantum dots grown on nonconventionally oriented GaAs substrates. Journal of Crystal Growth, 1998, 187, 126-132.	1.5	30
116	Multiple gated InAs dot ensembles. Applied Physics Letters, 1999, 75, 671-673.	3.3	30
117	Hybrid magneto-electric states in resonant tunnelling structures. Superlattices and Microstructures, 1989, 5, 527-530.	3.1	29
118	Zero-dimensional states in macroscopic resonant tunneling devices. Applied Physics Letters, 1994, 64, 2563-2565.	3.3	29
119	Spectral analysis of InGaAs/GaAs quantum-dot lasers. Applied Physics Letters, 1999, 75, 2169-2171.	3.3	29
120	Advances in self-assembled semiconductor quantum dot lasers. Microelectronics Journal, 2005, 36, 950-956.	2.0	29
121	Ultrafast Strain-Induced Current in a GaAs Schottky Diode. Physical Review Letters, 2011, 106, 066602.	7.8	29
122	Revealing the nature of low-temperature photoluminescence peaks by laser treatment in van der Waals epitaxially grown WS ₂ monolayers. Nanoscale, 2018, 10, 4807-4815.	5.6	29
123	Zn diffusion-induced disorder in AlAs/GaAs superlattices. Semiconductor Science and Technology, 1989, 4, 841-846.	2.0	28
124	Surface acoustic wave attenuation by localized electrons in a 2DEG at a GaAs/AlGaAs heterojunction. Semiconductor Science and Technology, 1992, 7, 641-647.	2.0	28
125	Edge channels and the quantum-Hall-effect breakdown. Physical Review B, 1994, 49, 5379-5385.	3.2	28
126	Energy states of Be in GaAs. Physical Review B, 1996, 53, 12829-12834.	3.2	28

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127	Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. Journal of Applied Physics, 2001, 89, 6044-6047.	2.5	28
128	Evidence for sequential tunnelling and charge build-up in double barrier resonant tunnelling devices. Surface Science, 1988, 196, 404-409.	1.9	27
129	Annealing effects on Si-doped GaAs grown on high-index planes by molecular-beam epitaxy. Journal of Applied Physics, 1994, 75, 3151-3157.	2.5	27
130	Dynamic quantum-confined stark effect in self-assembled InAs quantum dots. Applied Physics Letters, 2001, 78, 931-933.	3.3	27
131	The resistance of two quantum point contacts in series. Journal of Physics Condensed Matter, 1989, 1, 7505-7511.	1.8	26
132	Electroluminescence investigations of electron and hole resonant tunneling in p-i-n double-barrier structures. Physical Review B, 1992, 45, 9513-9516.	3.2	26
133	$(2\text{Å}-4)/c(2\text{Å}-8)$ to $(4\text{Å}-2)/c(8\text{Å}-2)$ transition on GaAs(001) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 943.	1.6	26
134	Influence of high-index GaAs substrates on the growth of highly strained (InGa)As/GaAs heterostructures. Journal of Crystal Growth, 1999, 201-202, 276-279.	1.5	26
135	Micromachined III-V cantilevers for AFM-tracking scanning Hall probe microscopy. Journal of Micromechanics and Microengineering, 2003, 13, 124-128.	2.6	26
136	Thermal quenching of single localized excitons in GaInNAs layers. Applied Physics Letters, 2011, 98, .	3.3	26
137	Luminescence characterization of cerium doped yttrium gadolinium aluminate phosphors. Optical Materials, 2012, 34, 1921-1925.	3.6	26
138	A comprehensive study on the effects of gamma radiation on the physical properties of a two-dimensional WS ₂ monolayer semiconductor. Nanoscale Horizons, 2020, 5, 259-267.	8.0	26
139	Resonant tunnelling studies of magnetoelectric quantisation in wide quantum wells. Journal of Physics Condensed Matter, 1989, 1, 4865-4871.	1.8	25
140	Edge effects in a gated submicron resonant tunneling diode. Applied Physics Letters, 1992, 60, 2508-2510.	3.3	25
141	Phonoconductivity measurement of the phonon absorption by a two-dimensional hole gas in a GaAs heterojunction. Physical Review B, 1996, 54, 2019-2027.	3.2	25
142	Rashba spin-splitting of electrons in asymmetric quantum wells. Physical Review B, 2010, 82, .	3.2	25
143	Raman scattering by the E _{2h} and A ₁ (LO) phonons of In _x Ga _{1-x} N epilayers (0.25 < x < 0.75) grown by molecular beam epitaxy. Journal of Applied Physics, 2012, 111, 063502.	2.5	25
144	Probing the anisotropic dispersion of hole states in (100) and (311)A AlAs/GaAs/AlAs quantum wells. Semiconductor Science and Technology, 1994, 9, 298-309.	2.0	24

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145	Absence of long-range ordered reconstruction on the GaAs(311)A surface. <i>Physical Review B</i> , 1997, 55, 15397-15400.	3.2	24
146	Suppression of electron channelling in microscopic magnetic waveguides. <i>Physical Review B</i> , 2001, 64, .	3.2	24
147	Electrical rectification by magnetic edge states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 699-702.	2.7	24
148	Generation and detection of terahertz coherent transverse-polarized acoustic phonons by ultrafast optical excitation of GaAs $\hat{\cdot}$ AlAs superlattices. <i>Applied Physics Letters</i> , 2006, 88, 134112.	3.3	24
149	Surface-Enhanced Raman Spectroscopy Study of 4-ATP on Gold Nanoparticles for Basal Cell Carcinoma Fingerprint Detection. <i>Journal of Electronic Materials</i> , 2016, 45, 2563-2568.	2.2	24
150	Hole space $\hat{\cdot}$ charge buildup and evidence for sequential tunneling in p $\hat{\cdot}$ type double $\hat{\cdot}$ barrier resonant tunneling devices. <i>Applied Physics Letters</i> , 1992, 60, 1474-1476.	3.3	23
151	Evidence for quantum states corresponding to families of stable and chaotic classical orbits in a wide potential well. <i>Physical Review B</i> , 1995, 51, 18029-18032.	3.2	23
152	Energy relaxation by photoexcited carriers in the InAs/GaAs quantum-dot system: Bolometric detection of strong acoustic-phonon emission. <i>Applied Physics Letters</i> , 1999, 75, 3832-3834.	3.3	23
153	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. <i>Applied Physics Letters</i> , 2004, 84, 3046-3048.	3.3	23
154	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. <i>Physical Review B</i> , 2006, 74, .	3.2	23
155	Efficient light harvesting in hybrid CdTe nanocrystal/bulk GaAs p-i-n photovoltaic devices. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	23
156	Raman scattering reveals strong LO-phonon-hole-plasmon coupling in nominally undoped GaAsBi: optical determination of carrier concentration. <i>Optics Express</i> , 2014, 22, 11680.	3.4	23
157	Characterisation of temperature dependent parameters of multi-quantum well (MQW) Ti/Au/n-AlGaAs/n-GaAs/n-AlGaAs Schottky diodes. <i>Superlattices and Microstructures</i> , 2017, 111, 1010-1021.	3.1	23
158	Observation of the transition to an insulating state consistent with a Wigner solid in a high-density 2D hole gas. <i>Physica B: Condensed Matter</i> , 1993, 184, 95-99.	2.7	22
159	Edge phonoconductivity in a magnetically quantized two-dimensional electron gas. <i>Physical Review B</i> , 1994, 49, 2585-2594.	3.2	22
160	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	22
161	Raman scattering studies of strain effects in (100) and (311)B GaAs $\hat{\cdot}$ xBix epitaxial layers. <i>Journal of Applied Physics</i> , 2013, 114, 193516.	2.5	22
162	Visible to infrared low temperature luminescence of Er $^{3+}$, Nd $^{3+}$ and Sm $^{3+}$ in CaSnO $_{3}$ phosphors. <i>Applied Radiation and Isotopes</i> , 2015, 99, 69-76.	1.5	22

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163	Quantum-resolved investigations of flux dynamics: Collective and single vortex effects. <i>Physical Review Letters</i> , 1993, 71, 3854-3857.	7.8	21
164	Resonant tunneling and photoluminescence spectroscopy in quantum wells containing self-assembled quantum dots. <i>Journal of Applied Physics</i> , 2000, 88, 2005-2012.	2.5	21
165	Study of electron-hole generation and recombination in semiconductors using the Osaka free electron laser. <i>Physica B: Condensed Matter</i> , 2002, 314, 431-436.	2.7	21
166	Voltage-controlled hole spin injection in nonmagnetic GaAs/AlAs resonant tunneling structures. <i>Physical Review B</i> , 2006, 73, .	3.2	21
167	Numerical simulation of bias and photo stress on indium gallium zinc-oxide thin film transistors. <i>Vacuum</i> , 2015, 120, 59-67.	3.5	21
168	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. <i>Semiconductor Science and Technology</i> , 1993, 8, 1465-1469.	2.0	20
169	Resonant tunnelling at far infra-red frequencies. <i>Journal of Physics Condensed Matter</i> , 1994, 6, 3945-3954.	1.8	20
170	Disorder-driven intermediate state in the lattice melting transition of Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ single crystals. <i>Physical Review B</i> , 1997, 56, R14295-R14298.	3.2	20
171	Scanning Hall probe microscopy of ferromagnetic structures. <i>Journal of Magnetism and Magnetic Materials</i> , 1999, 196-197, 917-919.	2.3	20
172	Nonlinear charging effect of quantum dots in a p ⁺ -i ⁺ -n diode. <i>Physical Review B</i> , 2003, 68, .	3.2	20
173	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. <i>Physical Review B</i> , 2007, 75, .	3.2	20
174	Structural and optical properties of dilute InAsN grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2010, 108, .	2.5	20
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